

Ultraviolet selective GaN based UV sensor

GUVA-S20ED (AG38As-SMD-s)



Features

- UVA selective photodiode
- Optimally suited for low-cost UV consumer applications
- Intrinsicy insensitive in the visible due to the wide-bandgap semiconductor material GaN
- Small SMD package (1608)
- 0,076 mm² active chip area
- High speed and low noise

Eigenschaften

- UVA selektive Photodiode
- Optimale Eignung für kostengünstige UVA-Messung
- Inhärent unempfindlich gegen sichtbares Licht durch GaN-Halbleiter mit hoher Bandlücke
- Kleines SMD Gehäuse (1608)
- 0,076 mm² aktive Chipfläche
- Schnelle Photodiode mit niedrigem Rauschen

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Maximum Ratings

Parameter	Symbol	Value	Unit
Operating temperature range	T_{opt}	-40 ... +90	°C
Reverse voltage	V_{Rmax}	5	V

General Characteristics

($T_a = 25\text{ °C}$)

Parameter	Symbol	Value	Unit
Active area	A	0,076	mm ²
max. Dark current at 1 V reverse bias	I_d	1	nA
Capacitance	C	45	pF
Short circuit current at bright sun	I_0	ca. 200	nA

Spectral Characteristics

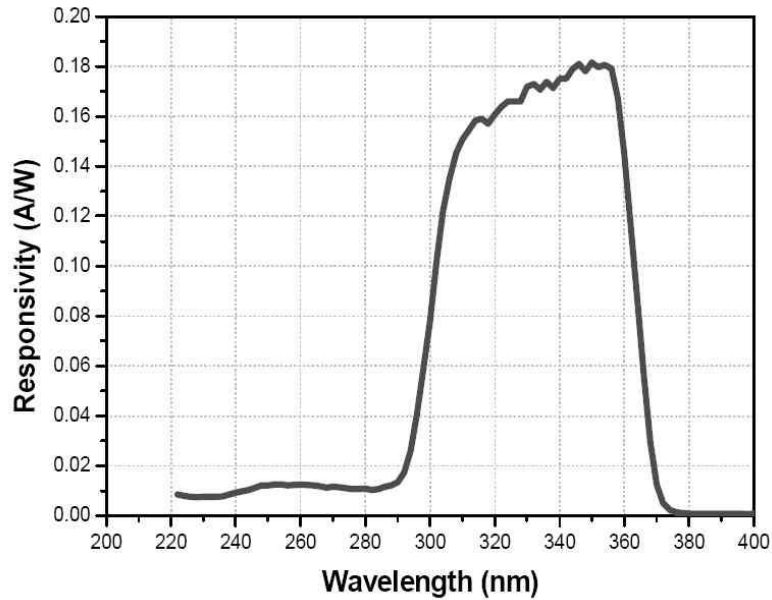
($T_a = 25\text{ °C}$)

Parameter	Symbol	Value	Unit
Responsivity	S_{max}	0,1	A W ⁻¹
Wavelength of max. spectral sensitivity	λ_{Smax}	350	nm
Range of spectral sensitivity ($S=0.1 \cdot S_{max}$)	-	290-375	nm

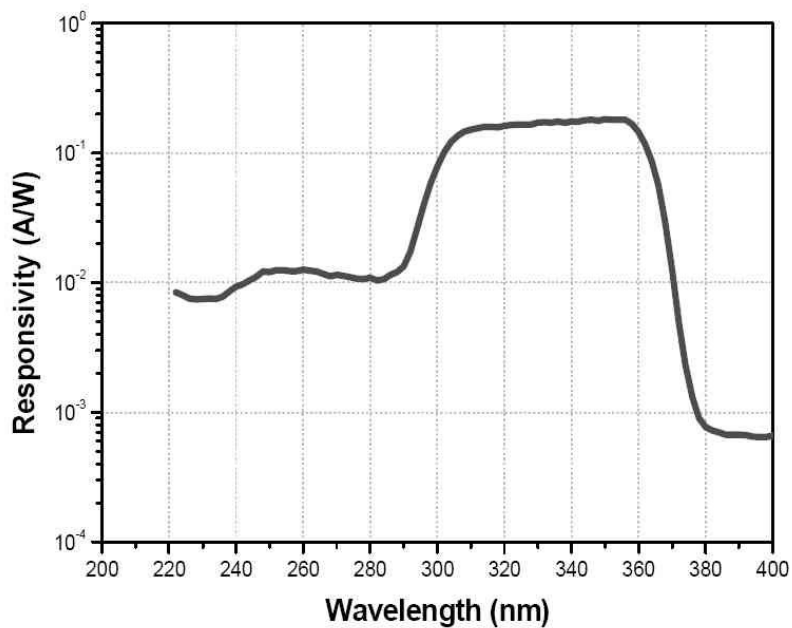
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Linear Spectral Response



Logarithmic Spectral Response

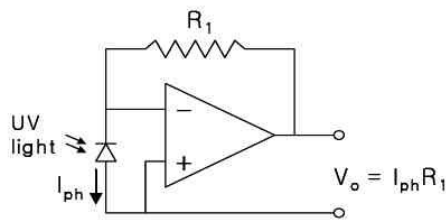


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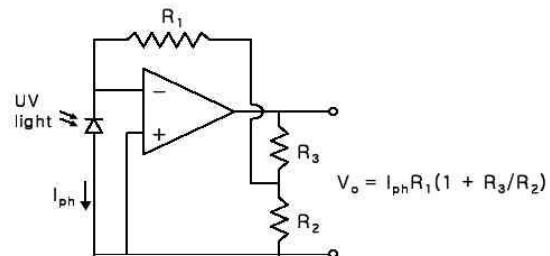


Application Examples

1. Basic Feedback Ammeter



2. Feedback Ammeter with Selective Voltage Gain



Pin Layout

